

FDA24N50 N-Channel UniFETTM MOSFET 500 V, 24 A, 190 mΩ

Features

- $R_{DS(on)}$ = 160 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 12 A
- Low Gate Charge (Typ. 65 nC)
- Low C_{rss} (Typ. 35 pF)
- 100% Avalanche Tested
- RoHS Compliant

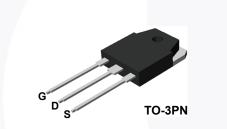
Applications

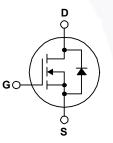
- PDP TV
- Uninterruptible Power Supply
- AC-DC Power Supply

FDA24N50 — N-Channel UniFETTM MOSFET

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter			Unit	
V _{DSS}	Drain to Source Voltage			500	V	
V _{GSS}	Gate to Source Voltage			±30	V	
ID	Drain Current	- Continuous (T _C = 25 ^o C)		24	Α	
		- Continuous (T _C = 100 ^o C)		14		
I _{DM}	Drain Current	- Pulsed	(Note 1)	96	Α	
E _{AS}	Single Pulsed Avalanche Energy (Note 2)			1872	mJ	
I _{AR}	Avalanche Current		(Note 1)	24	Α	
E _{AR}	Repetitive Avalanche En	ergy	(Note 1)	27	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)			4.5	V/ns	
P _D	Dower Dissinction	(T _C = 25 ^o C)		270	W	
	Power Dissipation	- Derate Above 25°C		2.2	W/ºC	
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C	

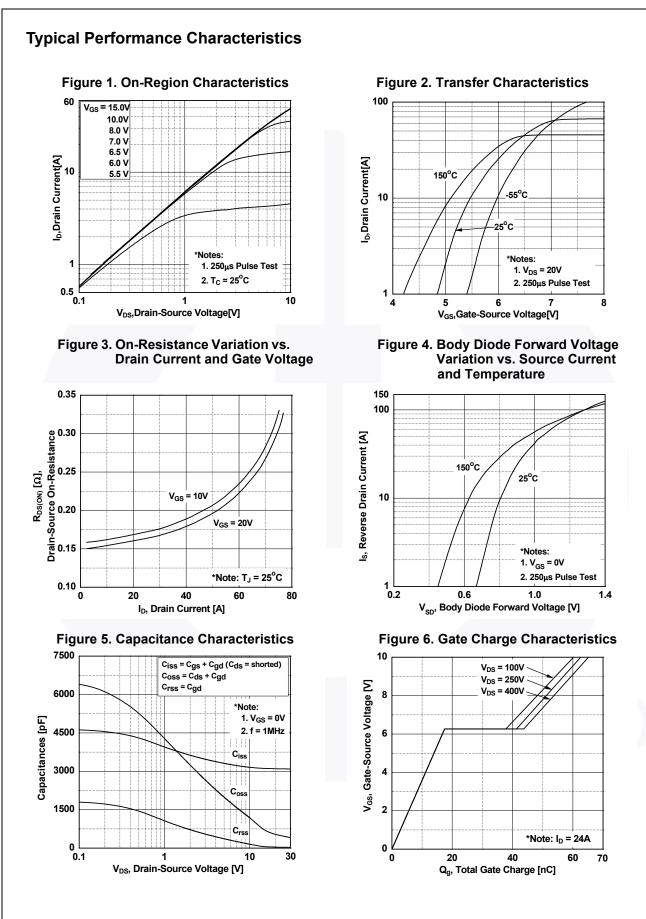
Thermal Characteristics

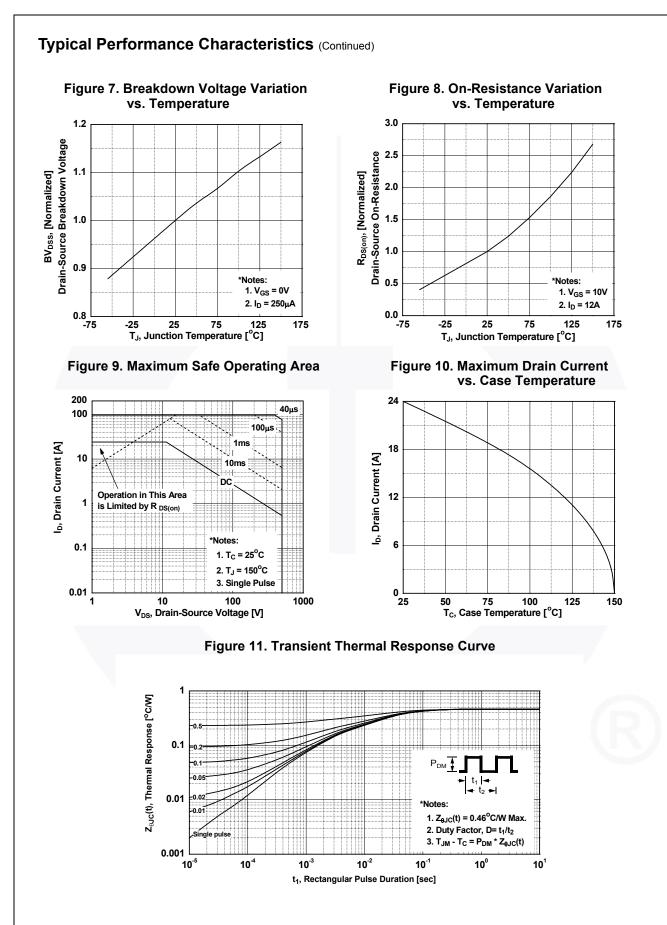
Symbol	Parameter	FDA24N50	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	0.46	°C/W
$R_{ ext{ heta}JA}$	Thermal Resistance, Junction to Ambient, Max.	40	°C/vv

FDA24N50
- N-Channel
UniFET TM
MOSFET

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Part Nu	ımber	Top Mark	Package	Packing Method	Reel Size	Ta	ape Width	Qu	antity
FDA24	1N50	FDA24N50	TO-3PN	Tube	N/A		N/A	30 units	
Electric	al Char	acteristics T _c = 25°C	unless othe	rwise noted.					
Symbol		Parameter		Test Conditions	5	Min.	Тур.	Max.	Unit
Off Charad	cteristics	1			i				
BV _{DSS}	Drain to Source Breakdown Voltage		lo =	I _D = 250 μA, V _{GS} = 0 V, T _J = 25 ^o C			-	_	V
ABV _{DSS}	Breakdown Voltage Temperature					500			
$/\Delta T_J$	Coefficient		I _D =	$I_D = 250 \ \mu A$, Referenced to $25^{\circ}C$		-	0.66	-	V/ºC
	Zero Gat	te Voltage Drain Current		V _{DS} = 500 V, V _{GS} = 0 V		-	-	1	Δ
DSS	2010 04		-	= 400 V, T _C = 125 ^o C		-	-	10	μΑ
GSS	Gate to E	Gate to Body Leakage Current		s = ±30 V, V _{DS} = 0 V		-	-	±100	nA
On Charac	teristics	;							
/ _{GS(th)}	Gate Th	reshold Voltage	VG	_S = V _{DS} , I _D = 250 μA		3.0	-	5.0	V
R _{DS(on)}		ain to Source On Resistance		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 12 \text{ A}$		-	0.16	0.19	Ω
9FS	Forward	Transconductance		_s = 20 V, I _D = 12 A		-	28	-	S
Dynamic (haracte	ristics					<u> </u>		
C _{iss}		pacitance				-	3120	4150	pF
C _{oss}		apacitance		_s = 25 V, V _{GS} = 0 V,		<u> </u>	460	615	pF
S _{rss}	-	Transfer Capacitance	f = '	1 MHz	-	-	35	52	p. pF
$Q_{g(tot)}$		te Charge at 10V	V	V _{DS} = 400 V, I _D = 24 A,		-	65	85	nC
Q_{gs}		Gate to Source Gate Charge Gate to Drain "Miller" Charge		$V_{\rm GS} = 400$ V, $I_{\rm D} = 24$ A, $V_{\rm GS} = 10$ V		-	18	-	nC
Q _{gd}				(Note 4)			26	-	nC
Switching	Charact	orietice			E				
-						-	47	104	ns
d(on)	Turn-On Delay Time Turn-On Rise Time		Vor	V _{DD} = 250 V, I _D = 24 A,		-	108	226	ns
d(off)		Delay Time		$V_{GS} = 10 \text{ V}, \text{ R}_{G} = 25 \Omega$			164	338	ns
f		Turn-Off Fall Time		(Note 4)			86	182	ns
					()				
		e Characteristics			i		II		1
s	Maximum Continuous Drain to Source D						-	24	A
SM		n Pulsed Drain to Source Dio	1			-	-	96	A
/ _{SD}		Source Diode Forward Voltag	00	$V_{GS} = 0 V, I_{SD} = 24 A$		-	-	1.4	V
n 2		Reverse Recovery Time Reverse Recovery Charge		$V_{GS} = 0 V, I_{SD} = 24 A,$			540		ns
Q _{rr}	Reverse	Recovery Charge	uiF/	dI _F /dt = 100 A/µs		-	8.1	-	μC
otes: . Repetitive rating	g: pulse-width li	imited by maximum junction temperatu	ıre.						
		50 V, $R_G = 25 \Omega$, starting $T_J = 25^{\circ}C$.							
		$_{DD} \le BV_{DSS}$, starting T _J = 25°C. erating temperature typical characteris	tics.						



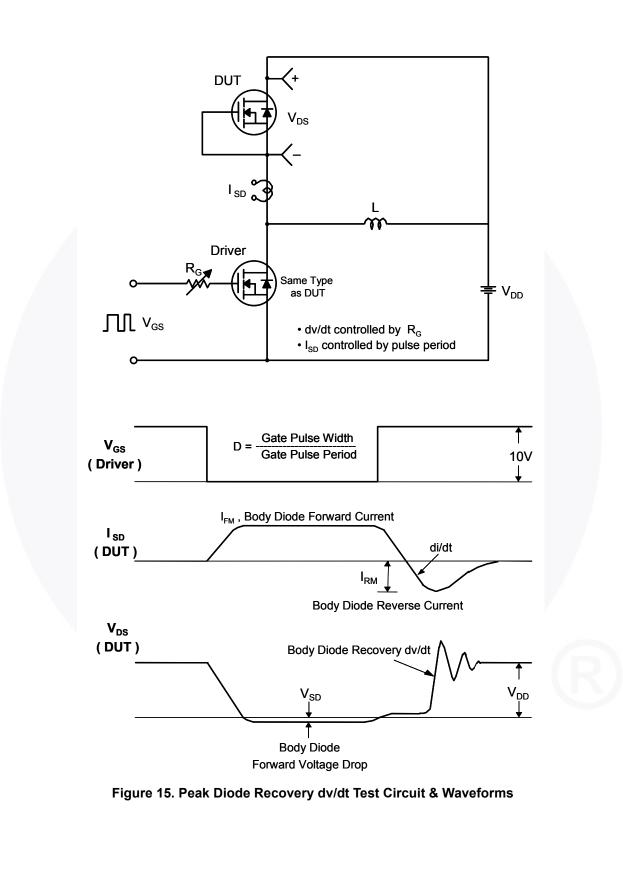


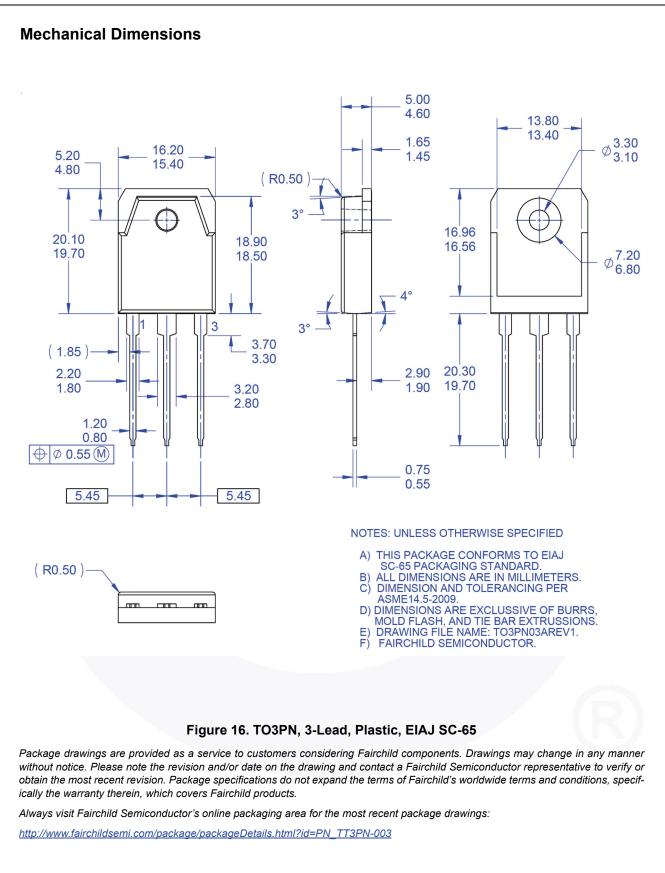
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 V_{GS} ξ ק Q_g V_{DS} Q_{gd} Q_{gs} • DUT I_G = const. Charge Figure 12. Gate Charge Test Circuit & Waveform R VDS V_{DS} 90% ο V_{DD} GS R_{G} 10% V_{GS} DUT V_{GS} ∏ 0 Figure 13. Resistive Switching Test Circuit & Waveforms L $E_{AS} = \frac{1}{2} L I_{AS}^2$ V_{DS} $\mathsf{BV}_{\mathsf{DSS}}$ ID o AS R_{G} **∔** ∨_{DD} $I_{D}(t)$ V_{GS} $V_{DS}(t)$ V_{DD} DUT Time t_p Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

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